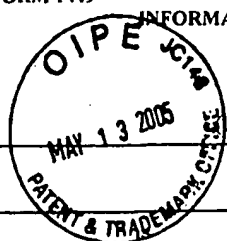


FORM 1449* INFORMATION DISCLOSURE STATEMENT IN AN APPLICATION (Use several sheets if necessary)	Docket Number: 3165.41USU1	Application Number: 10/723,382
	Applicant: MUNNS	
	Filing Date: 11/25/2003	Group Art Unit: 2815



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EXAMINER INITIAL	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
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EXAMINER <i>Maister Wane</i>	DATE CONSIDERED <i>5/12/06</i>
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<i>MEW</i>	6,583,454 B2	06/24/2003	Sheppard et al.				
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						YES	NO
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new		Smorchkova, I. et al., "AlN/GaN and (Al,Ga)N/AlN/GaN two-dimensional electron gas structures grown by plasma-assisted molecular-beam epitaxy," <i>Journal of Applied Physics</i> , Vol. 90, No. 10, pp. 5196-5201 (November 15, 2001)
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